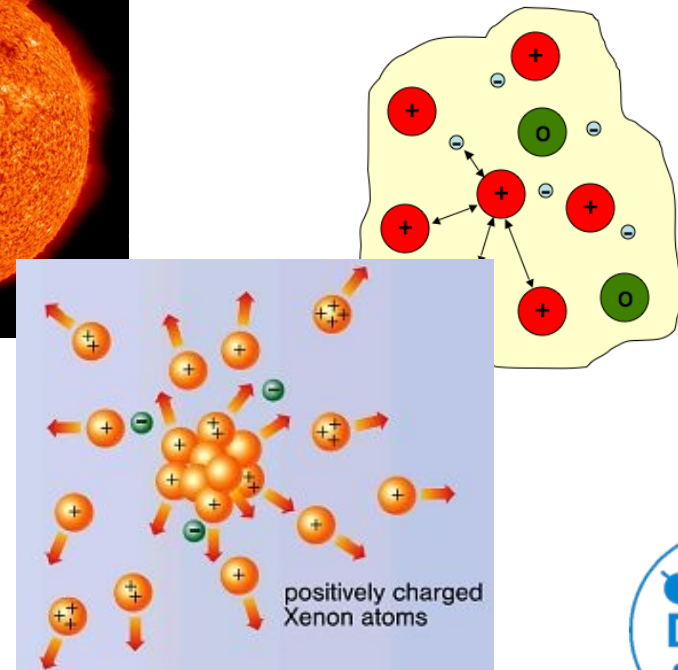
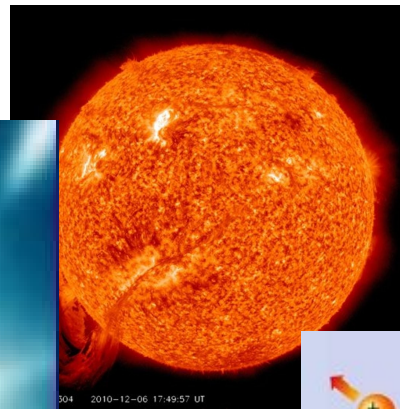
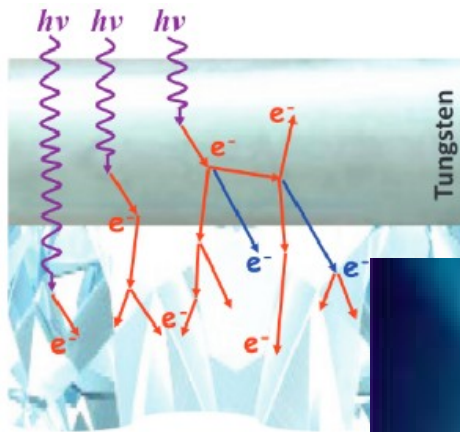


# Ultrafast transformation in matter induced by intense X-ray radiation - part I

B. Ziaja<sup>1,2</sup>

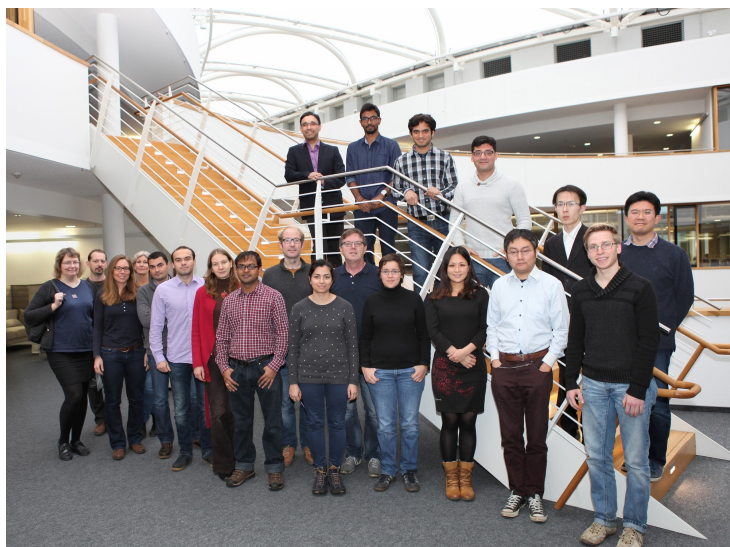
<sup>1</sup> Center for Free-Electron Laser Science, DESY, Hamburg

<sup>2</sup> Institute of Nuclear Physics, PAS, Kraków



# CFEL-DESY Theory Division at Center for Free-Electron Laser Science

The CFEL Theory Division develops theoretical and computational tools to predict the behavior of matter exposed to intense electromagnetic radiation. We employ quantum-mechanical and classical techniques to study ultrafast processes that take place on time scales ranging from  $10^{-12}$  s to  $10^{-18}$  s. Our research interests include the dynamics of excited many-electron systems; the motion of atoms during chemical reactions; and x-ray radiation damage in matter.



## Members of the CFEL-DESY Theory Division:

C. Arnold, S. Bazzi, Y.-J. Chen, O. Geffert, D. Gorelova, L. Inhester, Z. Jurek, K. Hanasaki, A. Hanna, A. Karamatskou, M. Krishna, Z. Li, M. A. Malik, N. Medvedev, P. K. Mishra, **R. Santra** (Division Director), V. Saxena, J. M. Slowik, S.-K. Son, V. Tkachenko, K. Toyota, O. Vendrell, B. Ziaja

## 3 subgroups: 'Ab-initio X-ray Physics'

(**R. Santra**), 'Chemical Dynamics' (**O. Vendrell**),  
'Modeling of Complex Systems' (**B. Ziaja**)

# Transitions in matter ...

**Energy delivered to a thermodynamic system → transition into a different phase or state of matter**

## Examples:

Structural transition → leads to a change of a system structure

Magnetic transition → changes magnetic properties (e.g., demagnetization)

Superconductivity → superconducting phase

...

Or

Solid-to-solid → leads to a change of solid's structure

Solid-to-liquid → melting

Solid-to-plasma → ionization

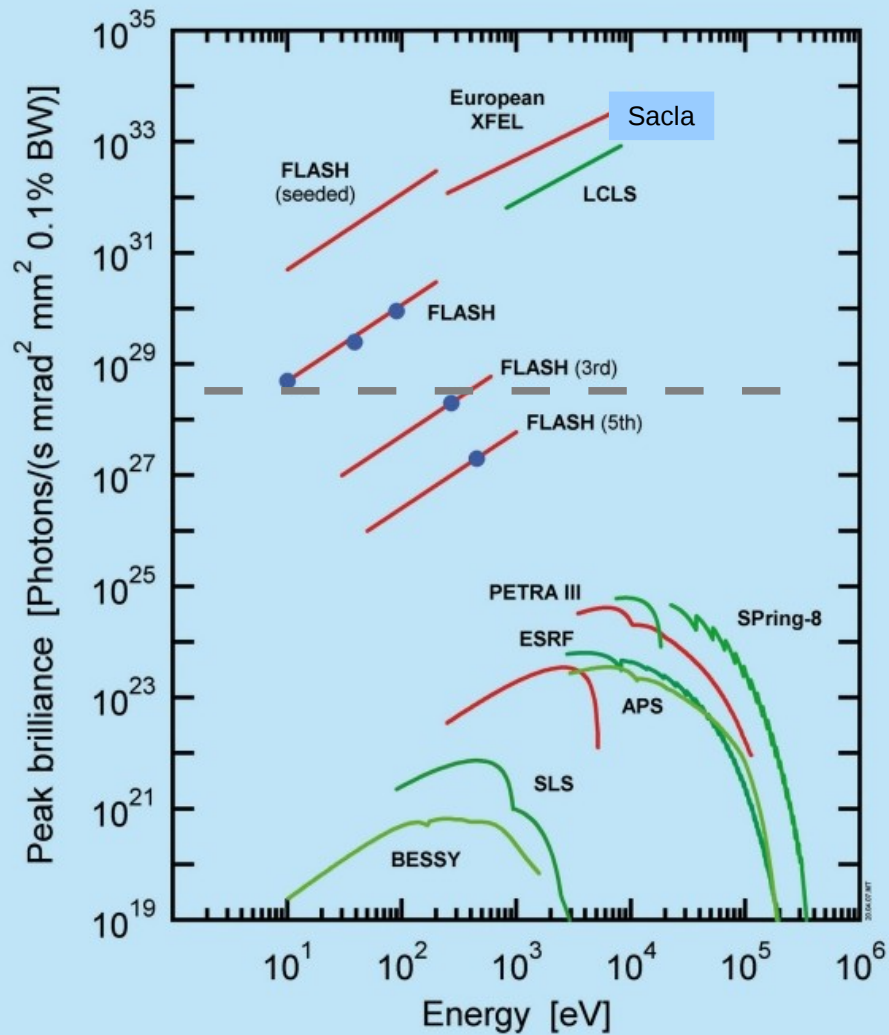
...

# Structural transitions in solids induced by X-ray radiation

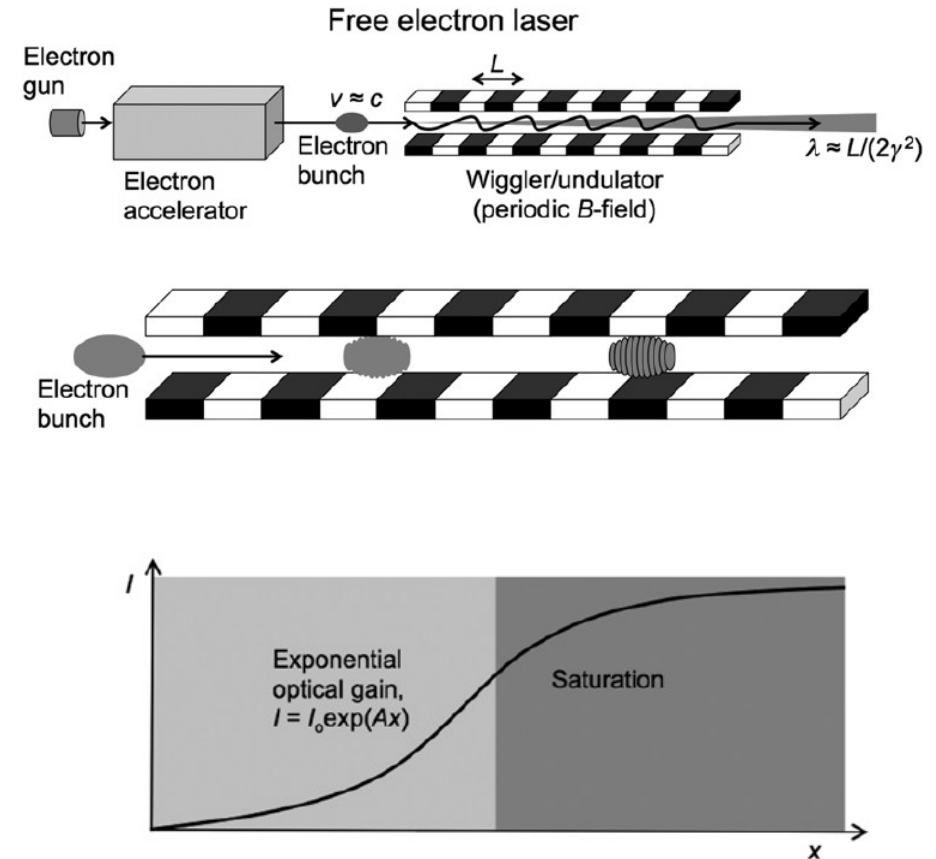
**... Femtosecond intense pulses  
from X-ray free-electron laser ...**



# FELs: 4<sup>th</sup> generation light sources



photon-science.desy.de



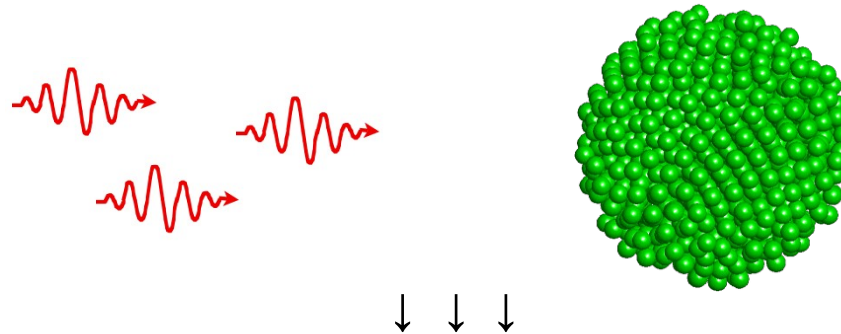
Ribic, Margaritondo, J. Phys. D **45** 213001 (2012)

Pulse duration ~ down to 10 fs  
Wavelength ~ VUV- hard X-ray



# Structural transitions in solids induced by X-ray radiation

Transition in irradiated solid depends on **material properties** and **pulse parameters** (photon energy, fluence, temporal/spatial pulse profile etc).

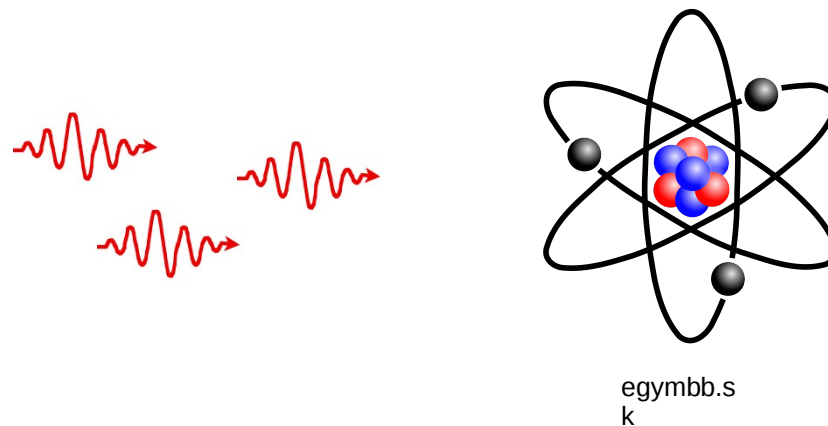


Pulse gets absorbed. This then 'translates' into the **average dose absorbed per atom**.

For X-rays there is no inverse bremsstrahlung → 'easy' control of energy absorption.

# Structural transitions in solids induced by X-ray radiation

**Transition depends on the average absorbed dose ....**



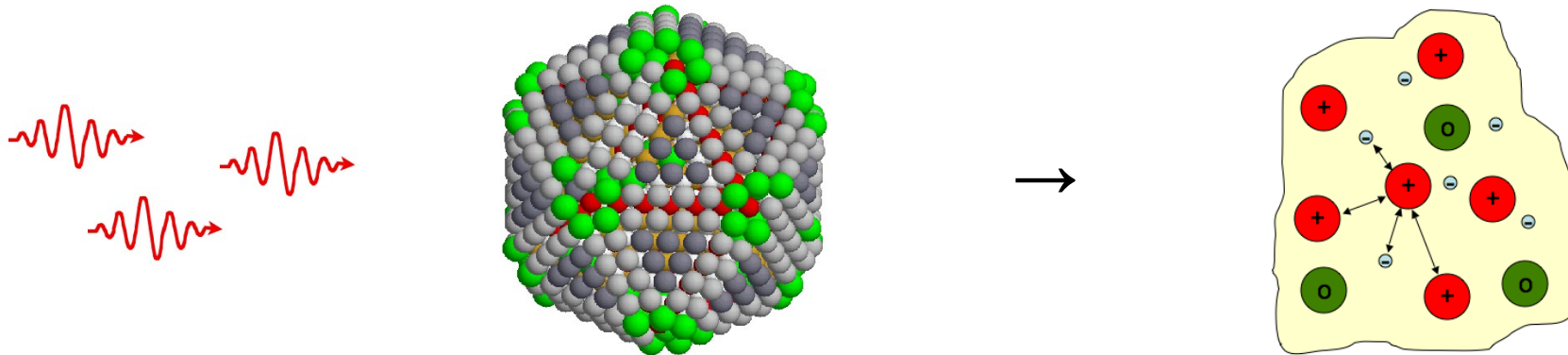


# Main interactions:

**X-ray photons:** elastic scattering, Compton scattering, photoionization (valence band, inner-shell), Auger decays

**Electrons:** collisional ionization and recombination from/to bands, thermalization → band modification

**Ions:** electrostatic repulsion → band modification → structural transition?



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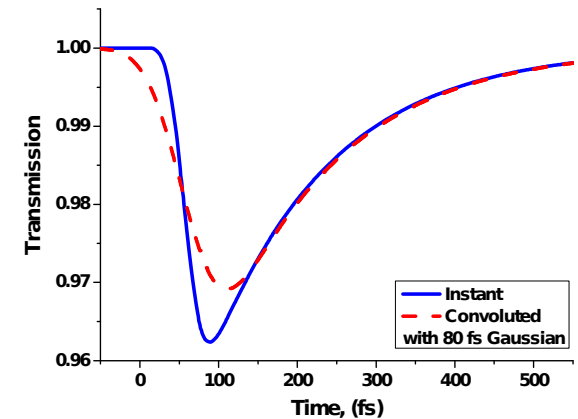
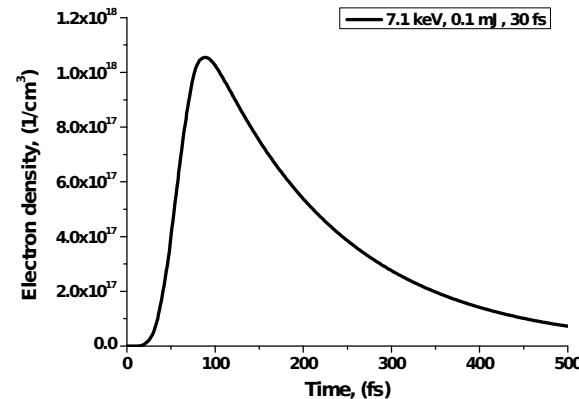


# Interaction of solids with low-fluence femtosecond X-ray pulses

## Low dose

Radiation excites **free electrons** within solids which induce transient change of solid's optical properties (reflectivity, transmission) but no structural changes.

Example:  
 $\text{SiO}_2$



Electron density translates into **transient change of optical properties** with Drude model or ab-initio calculated dielectric function

[Medvedev et al., CPP 53 (2013)

347]

→ application for a non-destructive high-resolution **FEL pulse timing tool**

**Damage Threshold**

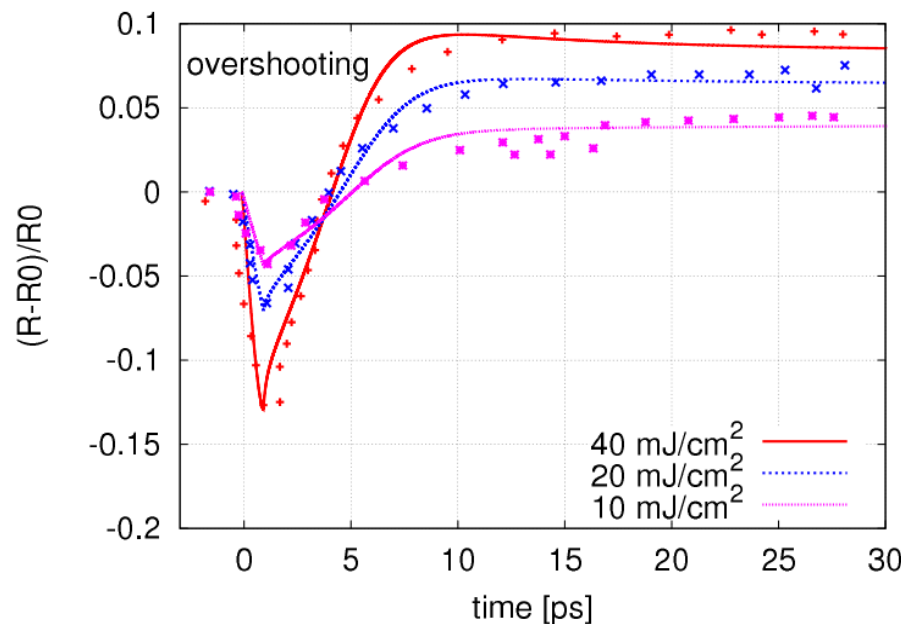
Harmand et al. (Medvedev, Ziaja), Nat. Phot. 7 (2013) 215;

Riedel et al. (Medvedev, Ziaja), Nat. Commun. 4 (2013) 1731

# Interaction of solids with low-fluence femtosecond X-ray pulses

Low dose

Reflectivity overshooting in GaAs



LCLS measurement (800 eV)

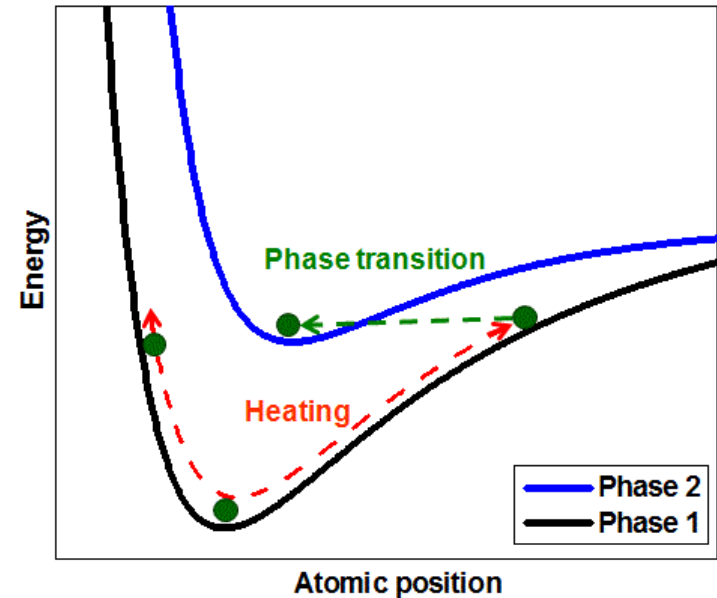
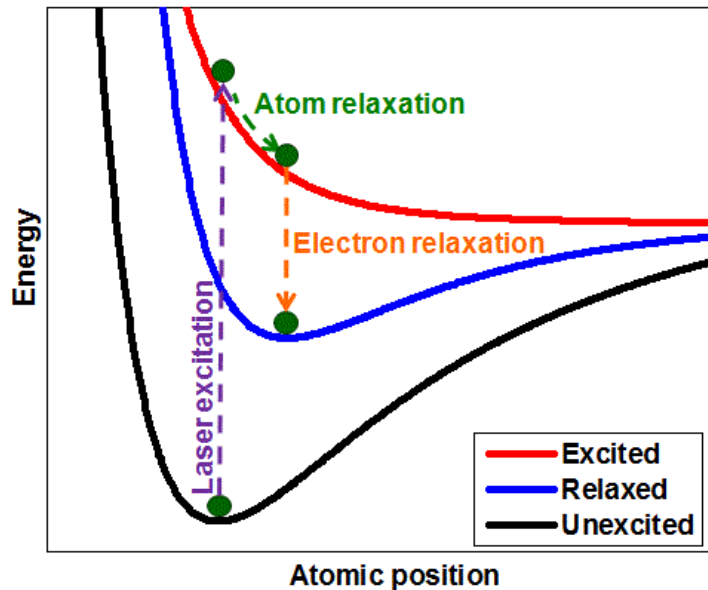
Damage Threshold

# Interaction of solids with femtosecond X-ray pulses of fluence above the damage threshold

Damage threshold

Non-thermal melting ( $\sim 100$  fs)

Thermal melting ( $\sim$  ps)



Change of interatomic potential

Heating of atomic lattice due to el-ph coupling within the same potential

Melting threshold

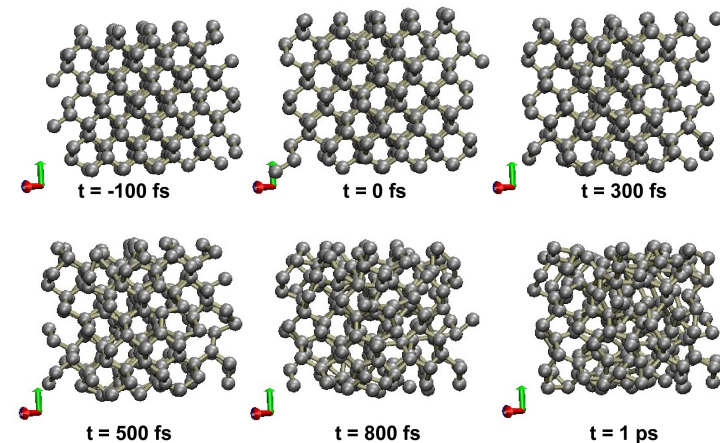
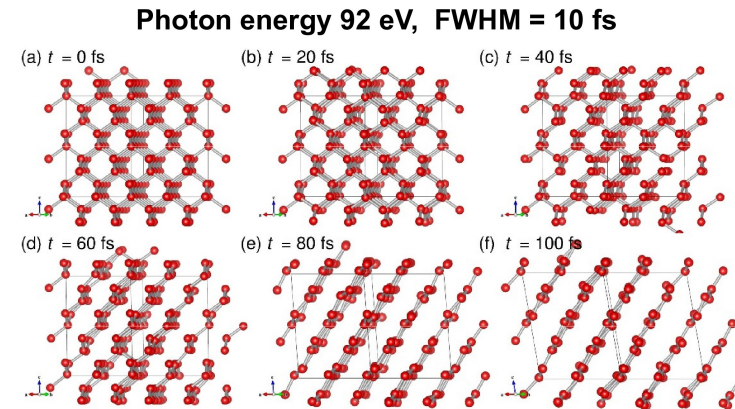
[Medvedev et al. (BZ): NJP 15 (2013) 015016;  
PRB 88 (2013) 224304 & 060101;  
PRB 91 (2015) 054113 ]

# Interaction of solids with femtosecond X-ray pulses of fluence above the damage threshold

Damage threshold    Structural transitions in solids:

→ **graphitization of diamond**  
ultrafast non-thermal process  
modeled within  
Born-Oppenheimer scheme

→ **amorphization of silicon**  
contribution of non-thermal  
and thermal melting (due to  
electron-phonon coupling);  
extended Born-Oppenheimer  
scheme



Melting threshold

[Medvedev et al. (BZ): NJP 15 (2013) 015016;  
PRB 88 (2013) 224304 & 060101;  
PRB 91 (2015) 054113 ]

Damage thresholds  
in good agreement  
with experiments!



beat

# Interaction of solids with femtosecond X-ray pulses of fluence above the damage threshold

Damage threshold

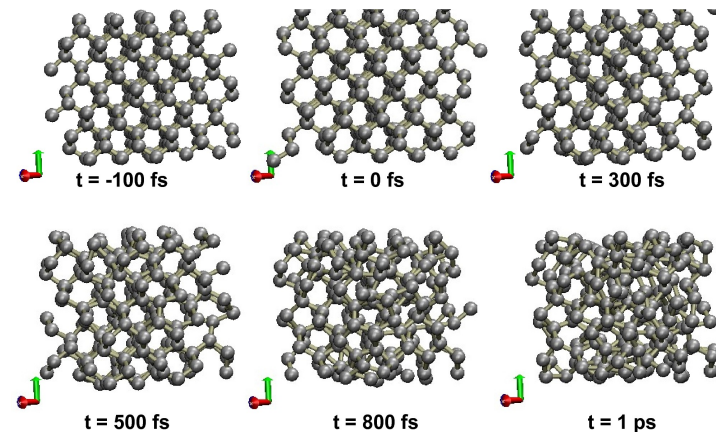
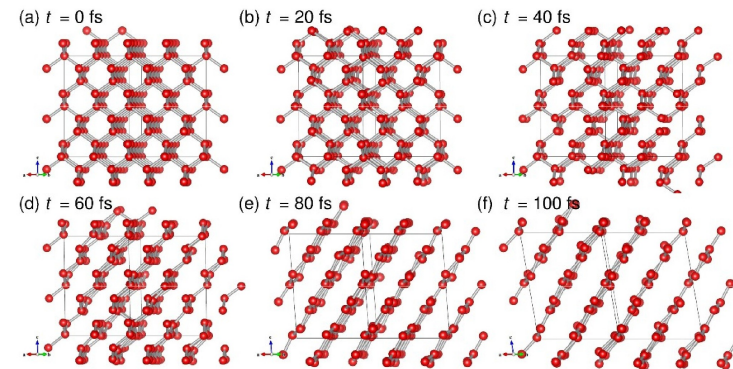
Simulations with dedicated code XTANT: X-ray induced Thermal and Non-Thermal Transitions  
[Medvedev et al.]



Melting threshold

[Medvedev et al. (BZ): NJP 15 (2013) 015016;  
PRB 88 (2013) 224304 & 060101;  
PRB 91 (2015) 054113 ]

Photon energy 92 eV, FWHM = 10 fs



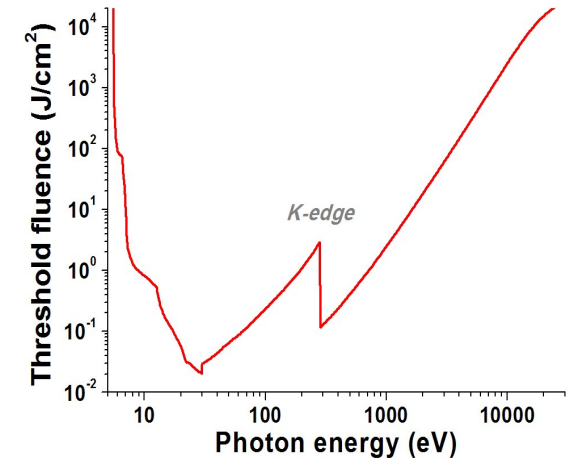
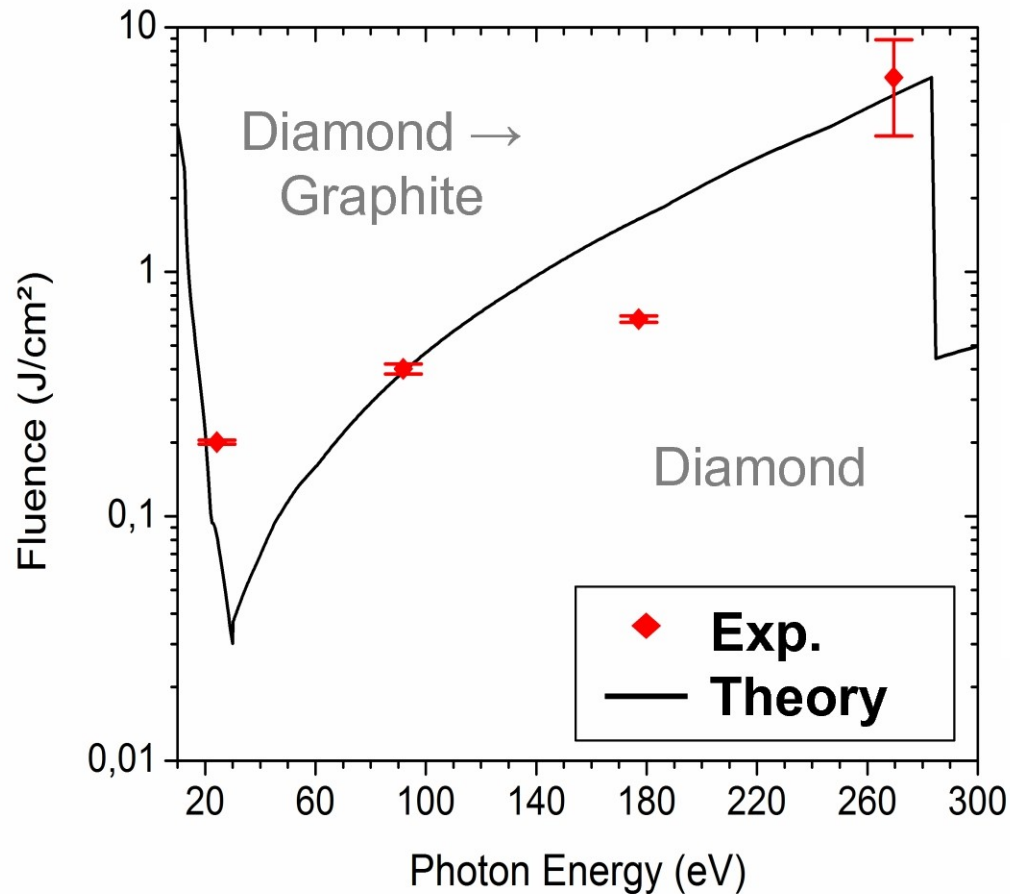
Damage thresholds  
in good agreement  
with experiments!





# Graphitization Damage threshold

Irradiated diamond turns into graphite if the fluence is high:



**Damage threshold is in a good agreement  
with the experiments by J. Gaudin *et al.* (FLASH)**

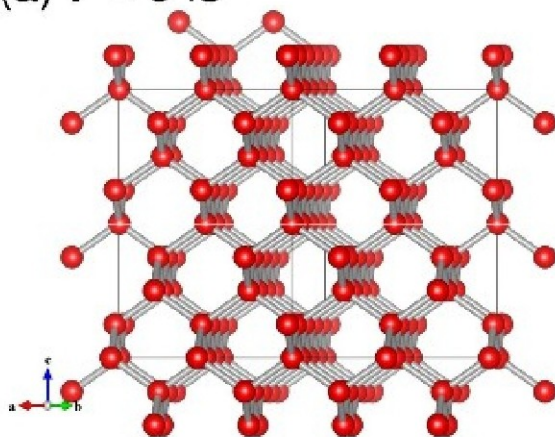
[J. Gaudin *et al.*, (2013) PRB, Rapid Comm. 88 (2013) 060101 (R)]

[N. Medvedev , H. Jeschke, BZ, PRB 88 (2013) 224304]

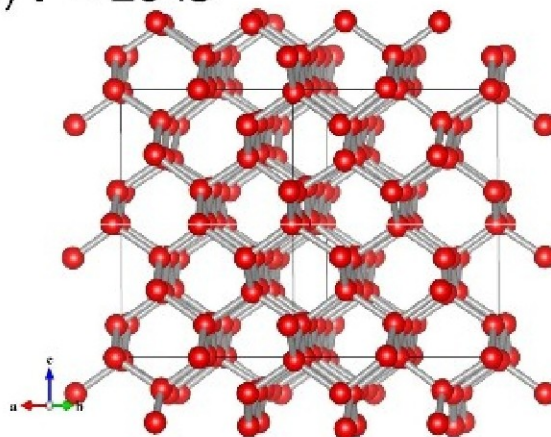
# Graphitization: Atomic snapshots

Photon energy 92 eV, FWHM = 10 fs

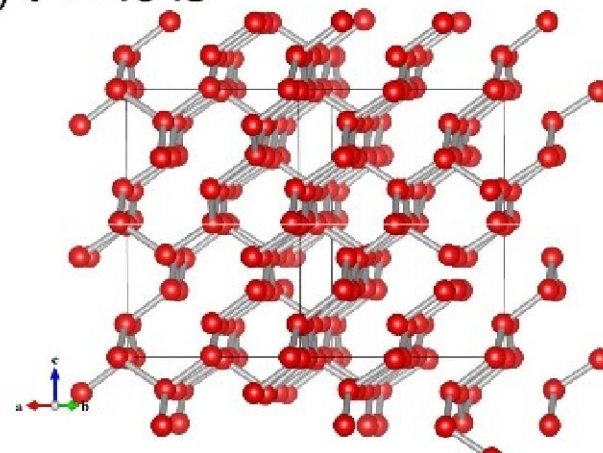
(a)  $t = 0$  fs



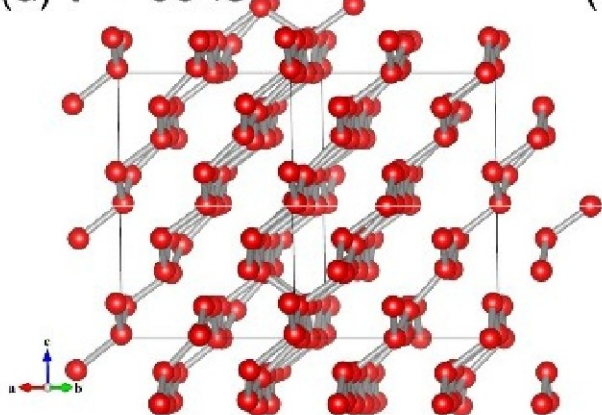
(b)  $t = 20$  fs



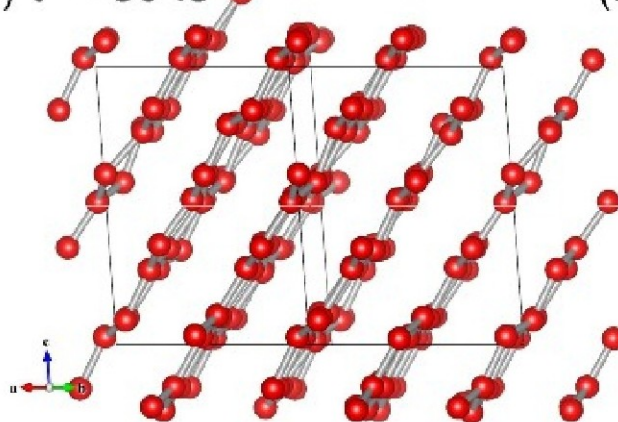
(c)  $t = 40$  fs



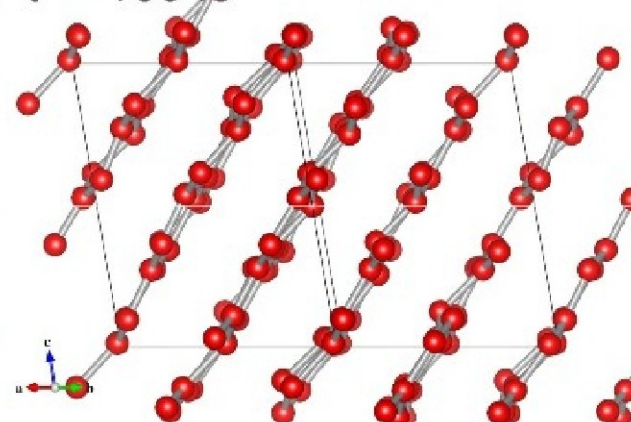
(d)  $t = 60$  fs



(e)  $t = 80$  fs



(f)  $t = 100$  fs



**Ultrafast graphitization of diamond**

[N. Medvedev, H. Jeschke, B. Ziaja, NJP 15 (2013) 015016]

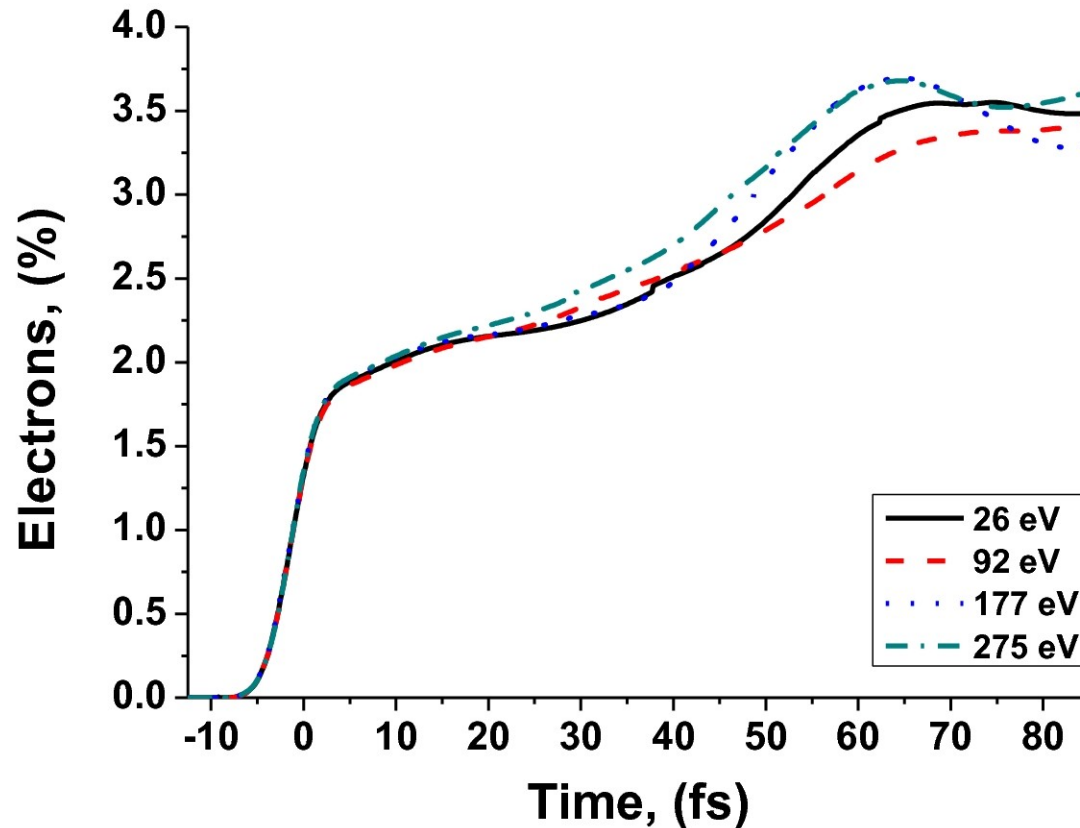
**Increase of electronic density → band gap collapse**





# Results: Conduction band electrons

Different photon energies: 26 eV, 92 eV, 177 eV, 275 eV

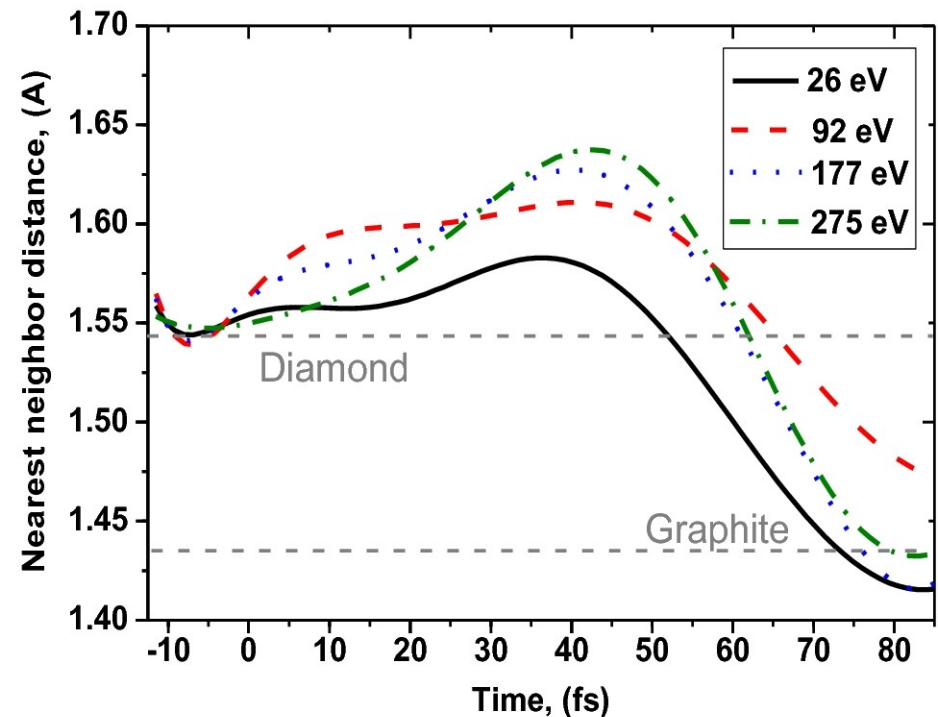
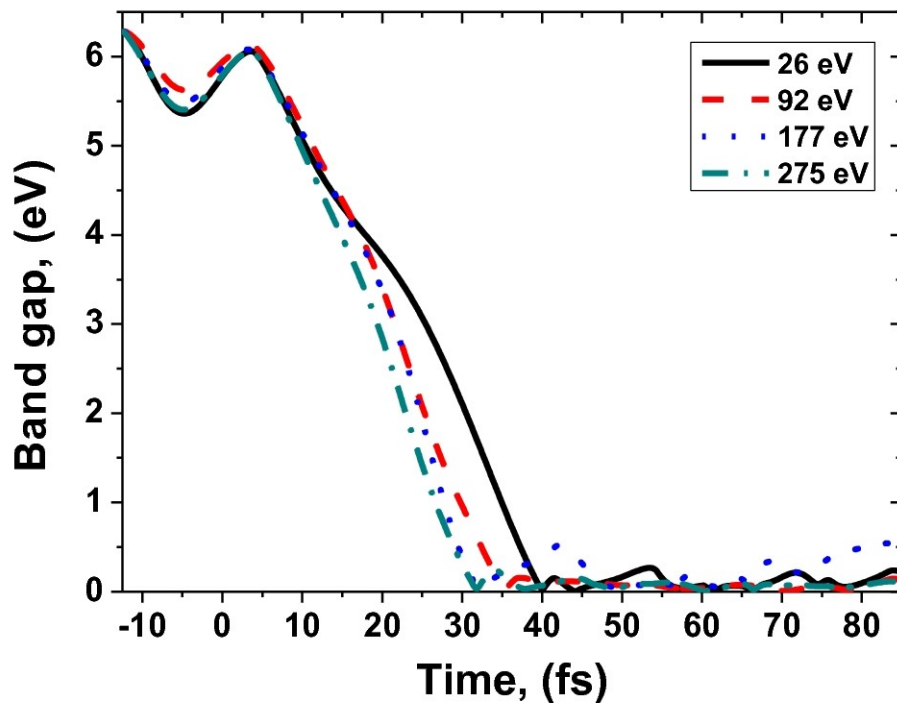


**When electron density overcomes threshold value of 1.5 %, phase transition occurs**



# Results: Bandgap collapse

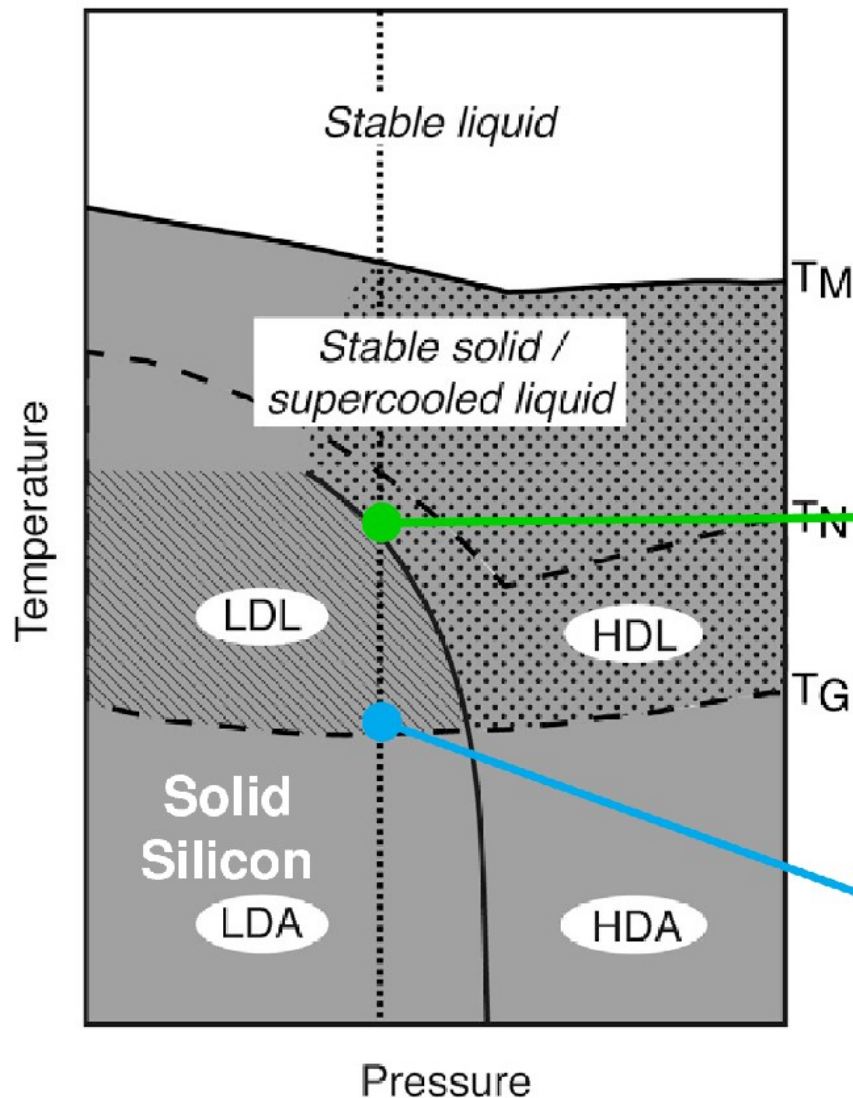
Different photon energies: 26 eV, 92 eV, 177 eV, 275 eV



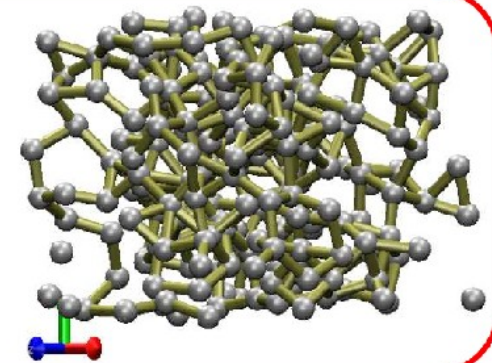
**Bandgap collapse induces ultrafast phase transition**

# Structural transition in Si: interplay of thermal and non-thermal processes

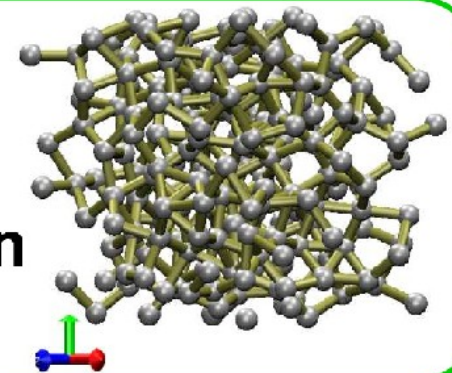
Silicon,  $\hbar\omega = 1$  keV, 10 fs



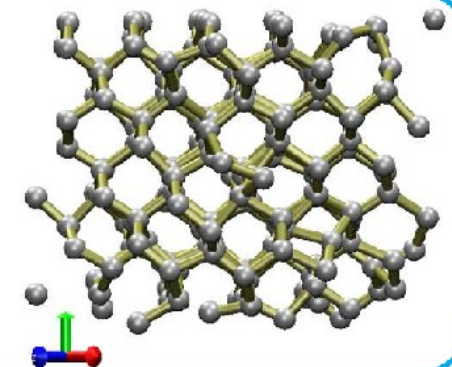
**Liquid**  
**2.1 eV/atom**



**HDL**  
**0.9 eV/atom**  
**Amorphization**



**LDL**  
**0.6 eV/atom**  
**Band gap collapse**

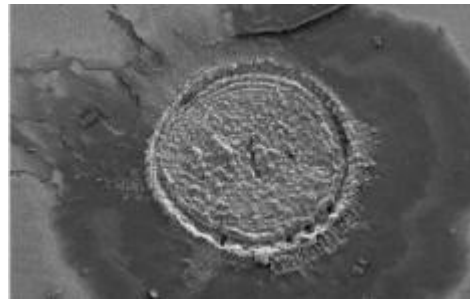


M. Beye, et al., *J. of El. Spectr.* 188 (2013) 172

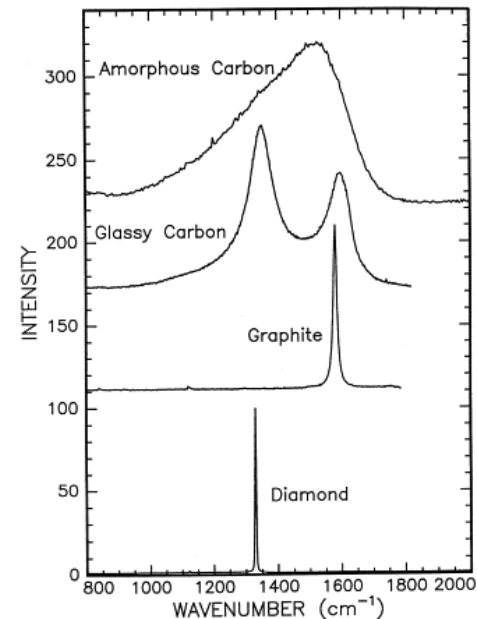
N. Medvedev, Z. Li, B. Ziaja, *PRB* 91 (2015) 054113

# Diagnostics of transitions?

Damage thresholds → post mortem measurements on samples



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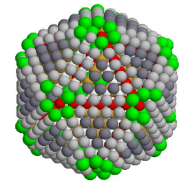
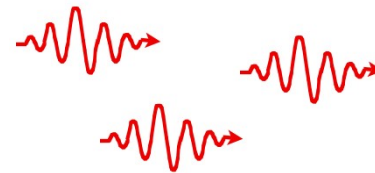
matsci4uwi.wordpress.com



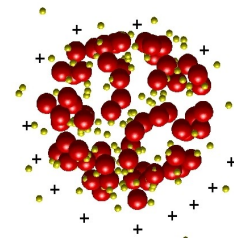
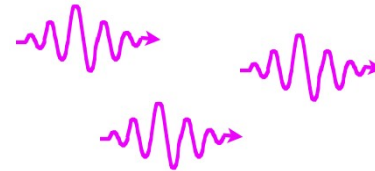
# Time-resolved diagnostics of transitions:

## Pump-probe experiments:

- pump pulse initiates transition ...



- probe pulse probes it at varying time delay ...



Ultrashort pulses from XFELs enable this!





# Transient optical properties as diagnostics of structural transitions within irradiated systems

## Low material excitation

below and around damage threshold → band structure evolution accurately described with **transferable tight binding method**



[V. Tkachenko, N. Mevedev et al.(BZ), PRB, in revision]

## Long-wavelength limit ( $q \rightarrow 0$ ), Tight-binding (TB) model

Optical **dielectric function** within the random-phase approximation (Lindhard formula) [3]:

$$\epsilon^{\alpha\beta}(E) = \delta_{\alpha,\beta} + \frac{4\pi e^2 \hbar^2}{m\Omega} \sum_{n,n'} (\eta_{n'} - \eta_n) \frac{F_{n,n'}^{\alpha\beta}}{E_{n,n'}} \left[ \frac{1}{E - E_{n,n'} + i\gamma} \right]$$

$$F_{n,n'}^{\alpha\beta} = \frac{2\langle n | \hat{p}_\alpha | n' \rangle \langle n' | \hat{p}_\beta | n \rangle}{mE_{n,n'}} \quad \text{- the oscillator strength [3]}$$

Calculated within tight-binding model by F. Trani et al, as:  $\mathbf{P}(\mathbf{R}, \mathbf{R}') = \frac{m}{i\hbar} [\mathbf{R} - \mathbf{R}'] H(\mathbf{R}, \mathbf{R}')$

Dielectric function → refractive indices  $n$ ,  $k$



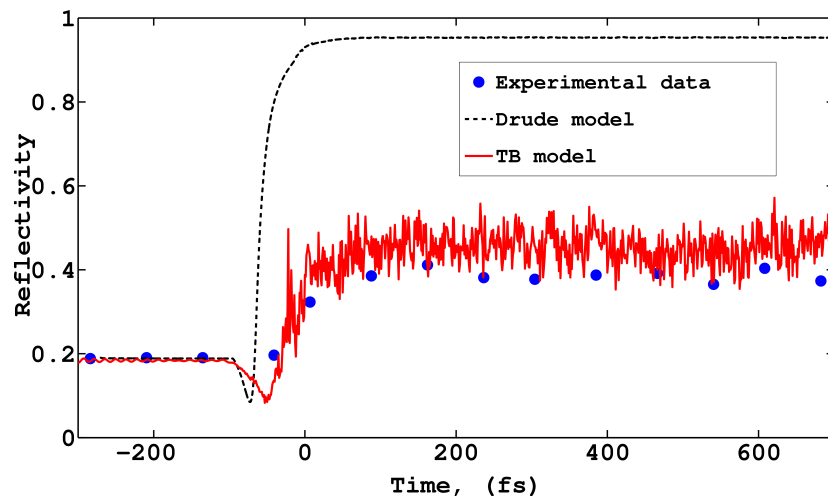
# Transient optical properties as diagnostics of structural transitions within irradiated systems

## Low material excitation

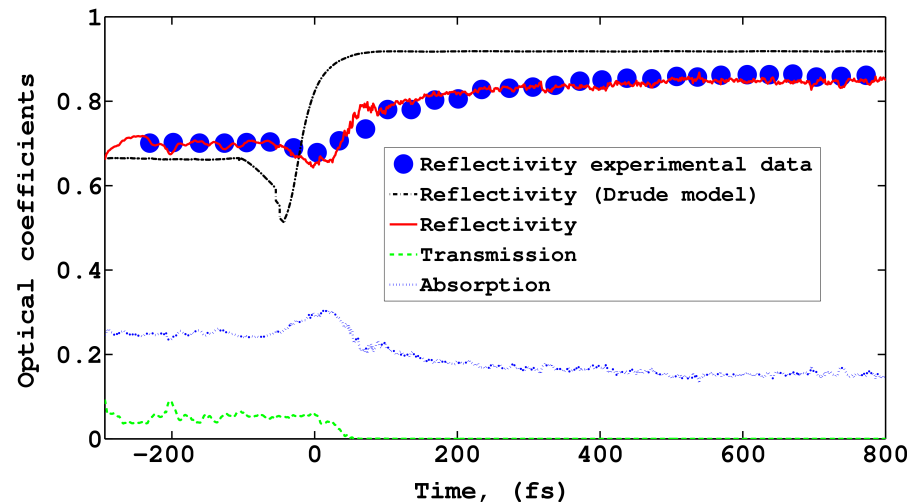
below and around damage threshold → band structure evolution accurately described with transferable tight binding method

[V. Tkachenko, N. Medvedev et al.(BZ), PRB, in revision]

- Diamond and silicon are excited with a laser pulse ...
- Transient optical properties are probed with the optical laser pulse ...
- Complex dielectric function calculated from an ab-initio scheme ...



Diamond



Silicon





# Transient optical properties as diagnostics of structural transitions within irradiated systems

**Low dose**      **Reflectivity overshooting in GaAs** ← effect of band gap shrinking

Timescales of relaxation and excitation processes.

Photoexcitation of electrons  
to conduction band (<10 fs)

Electron  
cascades

→ Thermalization of electrons  
& thermalization of holes  
(up to a few 100 fs)

→ Equilibration of electron  
& hole temperatures  
(up to 10 ps)

Electron-phonon  
interactions

→ Electron-lattice thermalization  
(~ few ps)

Electron-hole  
Recombination (~100 ns)

**Damage Threshold**

# Transient optical properties as diagnostics of structural transitions within irradiated systems

Low dose

## Reflectivity overshooting in GaAs

- Rate equations → the evolution of free-carrier densities as a function of time [5];

$$d n_{e-h}(t)/dt = \gamma_{e-h}(t)$$

← Before  $\Delta R/R$  minimum

$$d n_{e-h}(t)/dt = -\gamma_{rec} \cdot n_{e-h}(t)$$

← After  $\Delta R/R$  minimum

- Two-temperature model → electron-lattice equilibration

[5]; 
$$d T_{latt}(t)/dt = +G_{latt}(T_{e-h}(t) - T_{latt}(t))$$

$$d T_{e-h}(t)/dt = -G_{e-h}(T_{e-h}(t) - T_{latt}(t))$$

- Drude model → follows the transient reflectivity (extended for interband transitions) [5].

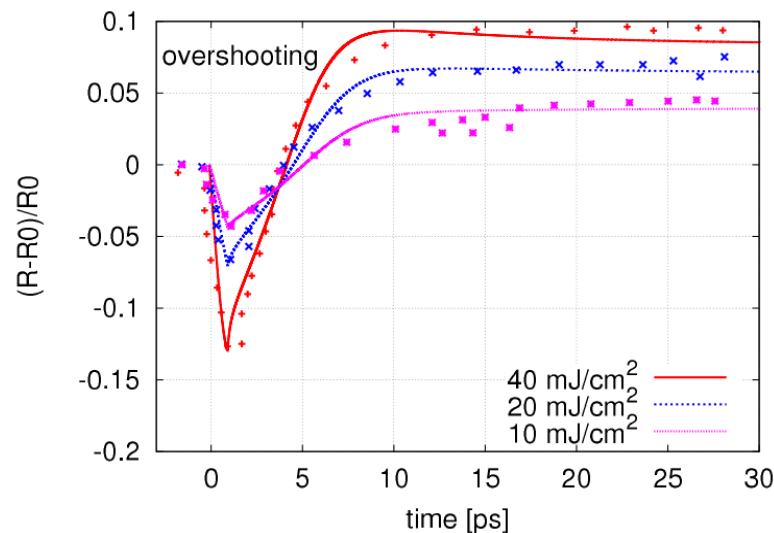
Damage Threshold

# Transient optical properties as diagnostics of structural transitions within irradiated systems

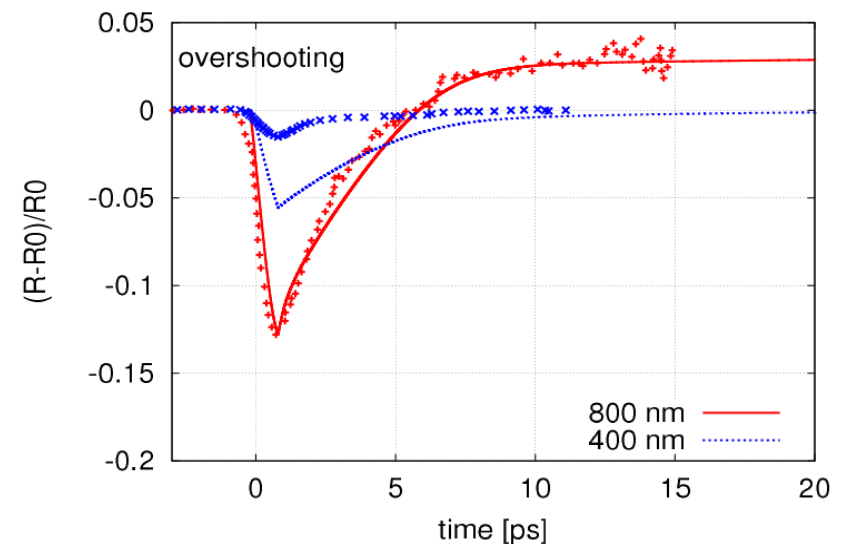
## Reflectivity overshooting in GaAs ← effect of band gap shrinking

Low dose

- Timescale of a few ps
- Observable at probe wavelength ~ band gap width (low absorption)
- Measurement of electron-phonon coupling with femtosecond resolution ( $\tau_{\text{el-latt}} \sim 2-3$  ps) and transient electronic temperatures ( $\sim 2-3$  eV)
- Expected for other narrow band-gap semiconductors



LCLS measurement (800 eV)



FLASH measurement (40 eV)

Damage Threshold

# Transient optical properties as diagnostics of warm dense matter formation

## Prospects:

Tight-binding method can be used only to **low-excited materials** ...

How about transition to **warm dense matter** after high material excitation?

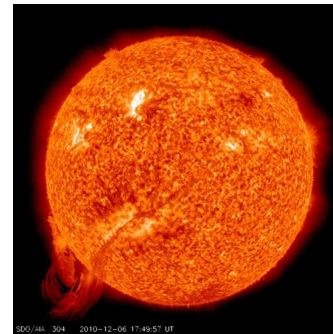


Dedicated **ab-initio method** needed to describe **non-equilibrium changes** within band structure ← adapted from XMOLECULE scheme?

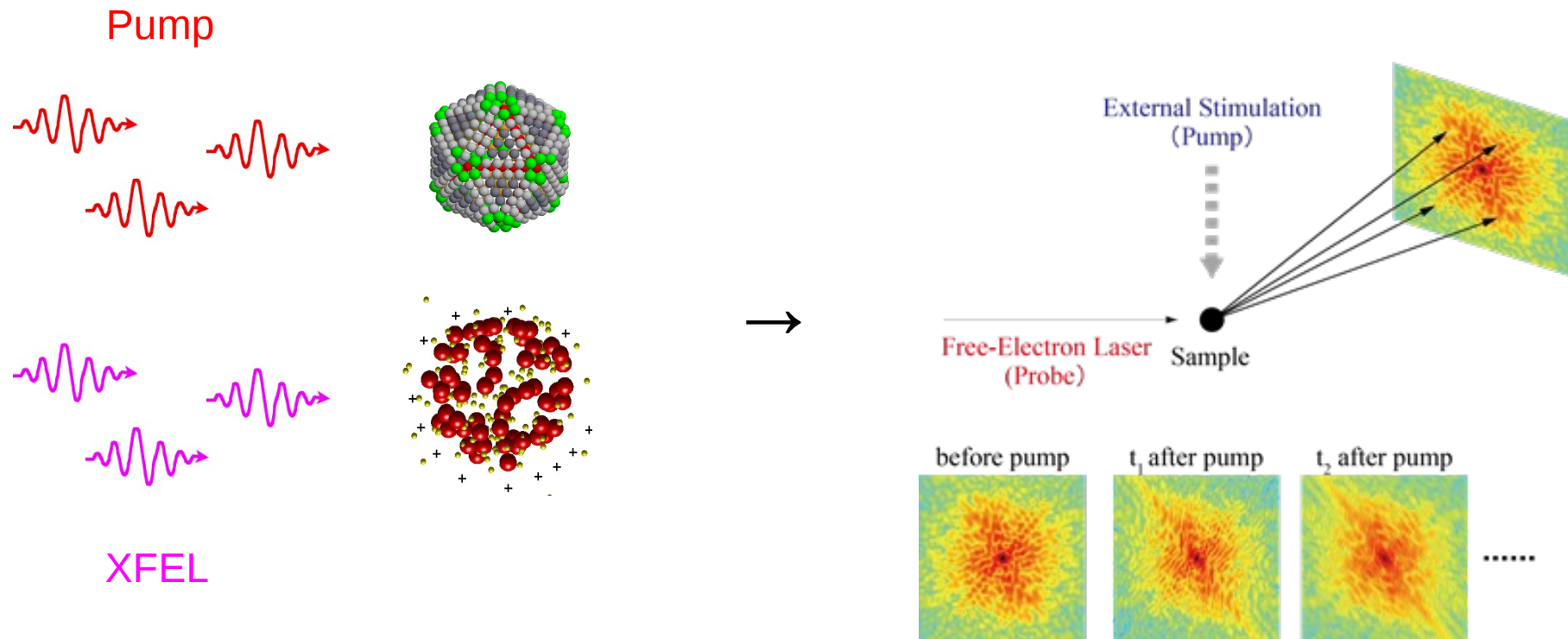


[Y. Hao et al., Str. Dyn. 2 (2015) 041707]

Transition can be monitored with **transient optical properties** ...



# X-ray diffraction as diagnostics of structural transitions within irradiated systems



[cxo-www.es.hokudai.ac.jp]

# Summary

**Transitions in solids induced by X-ray radiation depend on material properties and pulse parameters:**

- below damage threshold – **non-equilibrium electron kinetics**
- below melting threshold – **also rearrangement of atomic structure**
- above melting threshold – **amorphization; plasma, warm-dense matter formation**

**Time-resolved diagnostics of transitions**

- transient optical properties
- X-ray diffraction
- ...



# Thanking my collaborators and CFEL Theory Division

N. Medvedev    V. Tkachenko





# Thanking our external collaborators...

[J. Gaudin](#) (CELIA, Bordeaux)

[H. Jeschke](#) (U. Frankfurt), [Z. Li](#) (LCLS), [P. Piekarczyk](#) (INP, Kraków)

[L. Juha](#), [M. Stransky](#) (FZU, Prague), [R. Sobierajski](#) (IF PAN, Warszawa)

[H.-K. Chung](#) (IAEA, Vienna), [R. W. Lee](#) (LBNL, Berkley)

[M. Harmand](#) (LULI, CNRS), [M. Cammarata](#) (U. Rennes)

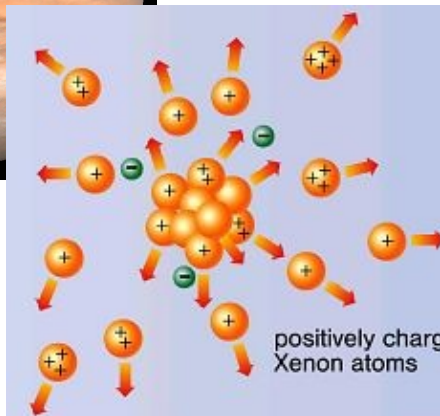
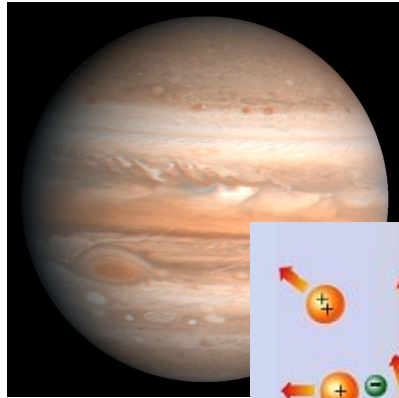
[T. Malezopoulos](#) (U. Hamburg)

[F. Tavella](#) (LCLS), [U. Teubner](#) (U. Oldenburg) and [FERMI team](#)

[S. Toleikis](#), [H. Hoepfner](#), [M. Prandolini](#), [T. Takanori](#) (DESY)

[W. Wurth](#) (DESY)

and ...



# Summary of codes

Atomic data and transitions rates from **XATOM** package (R. Santra & S. K. Son)

**Transport approach** → Boltzmann code: irradiation of atomic clusters with VUV and soft X-ray photons (B. Ziaja) → recently also extended to hard X-ray regime

**Hybrid MC-TBMD code XTANT** → modeling of structural changes in irradiated solids → applied to describe nonthermal melting in semiconductors (N. Medvedev) → transient optical properties (V. Tkachenko)

**Monte Carlo** model to follow ultrafast electron kinetics in X-rays irradiated solids (N. Medvedev); an element-flexible fast version **XCASCADE** → transient optical properties beyond Drude model

**Molecular Dynamics** code to follow classical ion and electron dynamics in X-ray irradiated clusters and macromolecules (Z. Jurek) → **XHYDRO**: its long-timescale extension (V. Saxena); on-the-fly coupling to XATOM working (S. K. Son)

Thank you for your attention !